

BF721T1G

PNP Silicon Transistor

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-300	Vdc
Collector - Base Voltage	V_{CBO}	-300	Vdc
Collector - Emitter Voltage	V_{CER}	-300	Vdc
Emitter - Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current	I_C	-50	mAdc
Total Power Dissipation up to $T_A = 25^\circ\text{C}$ (Note 1)	P_D	1.5	W
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

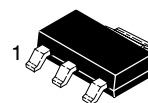
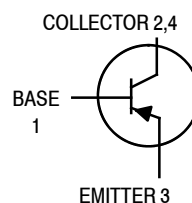
1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in².



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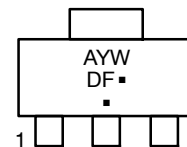
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PNP SILICON TRANSISTOR SURFACE MOUNT



SOT-223 (TO-261)
CASE 318E
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
DF = Device Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
BF721T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BF721T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = -1.0 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-300	-	Vdc
Collector-Base Breakdown Voltage ($I_C = -100 \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	-300	-	Vdc
Collector-Emitter Breakdown Voltage ($I_C = -100 \mu\text{Adc}$, $R_{BE} = 2.7 \text{ k}\Omega$)	$V_{(BR)CER}$	-300	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10 \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = -200 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	-10	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = -250 \text{ Vdc}$, $R_{BE} = 2.7 \text{ k}\Omega$) ($V_{CE} = -200 \text{ Vdc}$, $R_{BE} = 2.7 \text{ k}\Omega$, $T_J = 150^\circ\text{C}$)	I_{CER}	-	-50 -10	nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = -25 \text{ mAdc}$, $V_{CE} = -20 \text{ Vdc}$)	h_{FE}	50	-	-
Collector-Emitter Saturation Voltage ($I_C = -30 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)	$V_{CE(sat)}$	-	-0.8	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product ($V_{CE} = -10 \text{ Vdc}$, $I_C = -10 \text{ mAdc}$, $f = 35 \text{ MHz}$)	f_T	60	-	MHz
Feedback Capacitance ($V_{CE} = -30 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{re}	-	1.6	pF

BF721T1G

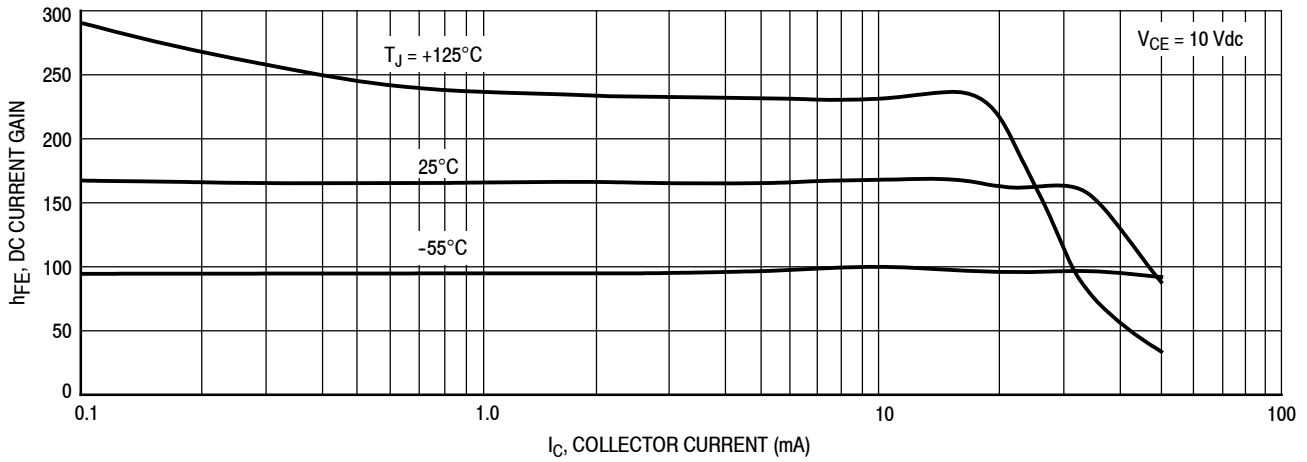


Figure 1. DC Current Gain

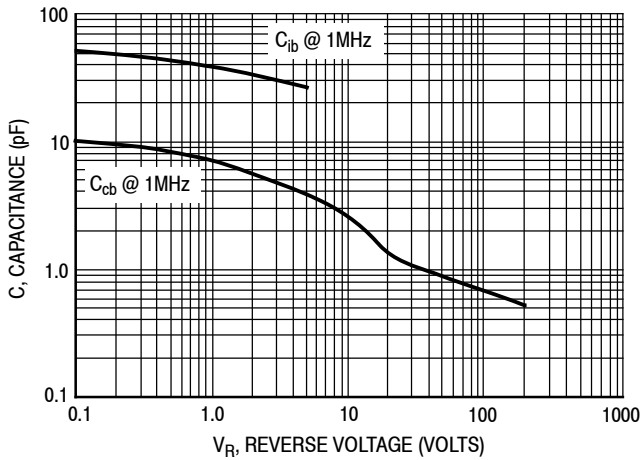


Figure 2. Capacitance

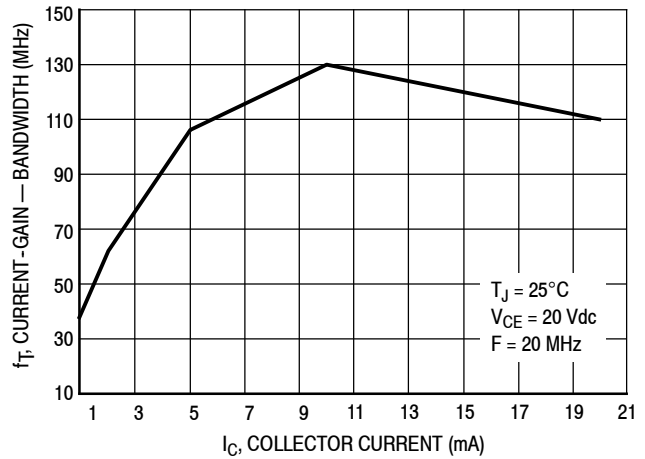


Figure 3. Current-Gain — Bandwidth

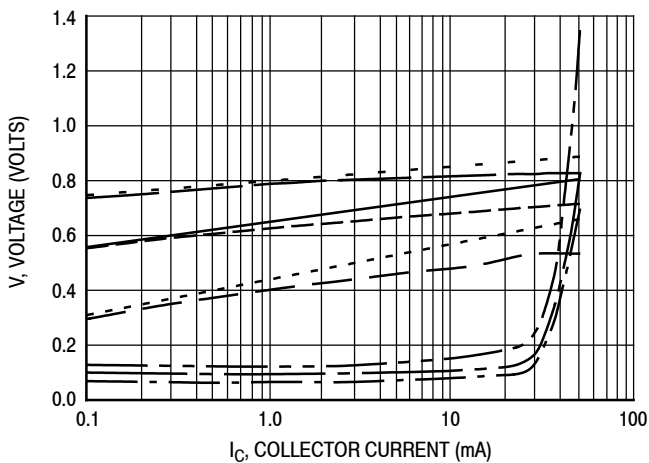


Figure 4. "ON" Voltages

- $V_{CE(sat)}$ @ 25°C , $I_C/I_B = 10$
- $V_{CE(sat)}$ @ 125°C , $I_C/I_B = 10$
- $V_{CE(sat)}$ @ -55°C , $I_C/I_B = 10$
- $V_{BE(sat)}$ @ 25°C , $I_C/I_B = 10$
- - - $V_{BE(sat)}$ @ 125°C , $I_C/I_B = 10$
- - - $V_{BE(sat)}$ @ -55°C , $I_C/I_B = 10$
- - - $V_{BE(on)}$ @ 25°C , $V_{CE} = 10 \text{ V}$
- - - $V_{BE(on)}$ @ 125°C , $V_{CE} = 10 \text{ V}$
- - - $V_{BE(on)}$ @ -55°C , $V_{CE} = 10 \text{ V}$

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

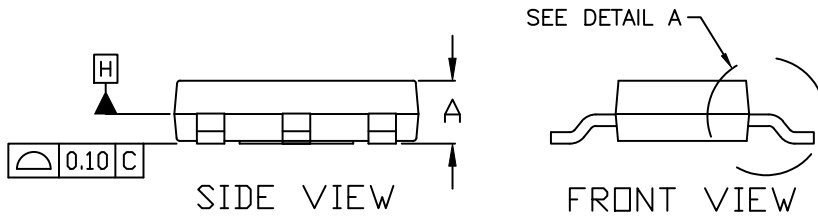
ON Semiconductor®



SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



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SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018

- | | | | | |
|--|---|---|---|---|
| STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. CATHODE
3. NC
4. CATHODE | STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN | STYLE 4:
PIN 1. SOURCE
2. DRAIN
3. GATE
4. DRAIN | STYLE 5:
PIN 1. DRAIN
2. GATE
3. SOURCE
4. GATE |
| STYLE 6:
PIN 1. RETURN
2. INPUT
3. OUTPUT
4. INPUT | STYLE 7:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2
4. CATHODE | STYLE 8:
CANCELLED | STYLE 9:
PIN 1. INPUT
2. GROUND
3. LOGIC
4. GROUND | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE |
| STYLE 11:
PIN 1. MT 1
2. MT 2
3. GATE
4. MT 2 | STYLE 12:
PIN 1. INPUT
2. OUTPUT
3. NC
4. OUTPUT | STYLE 13:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | | |

**GENERIC
 MARKING DIAGRAM***



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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